TO-252 P

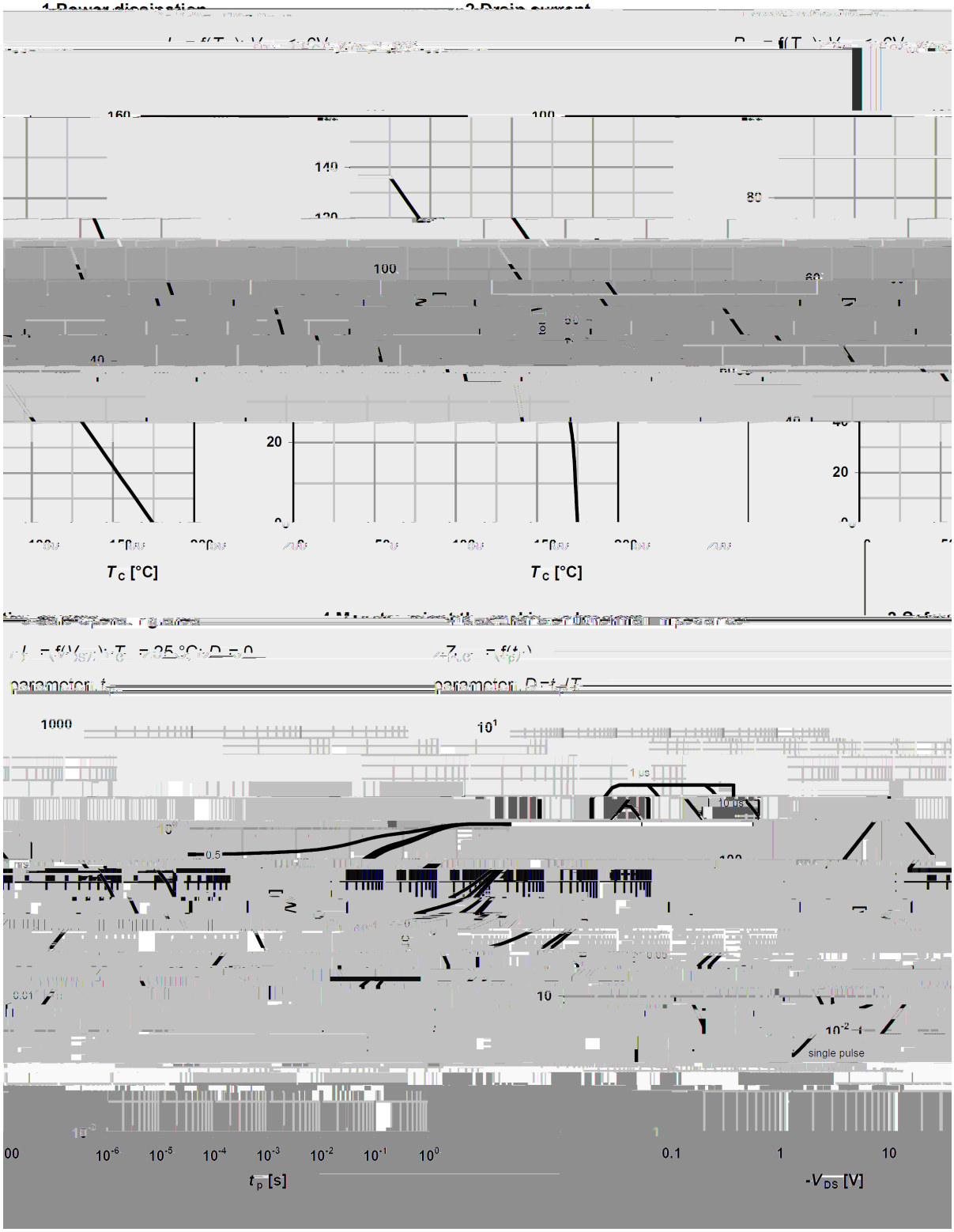
P-CHANNEL MOSFET in a TO-252 Plastic Package.

/ Electrical Characteristics(Ta=25)

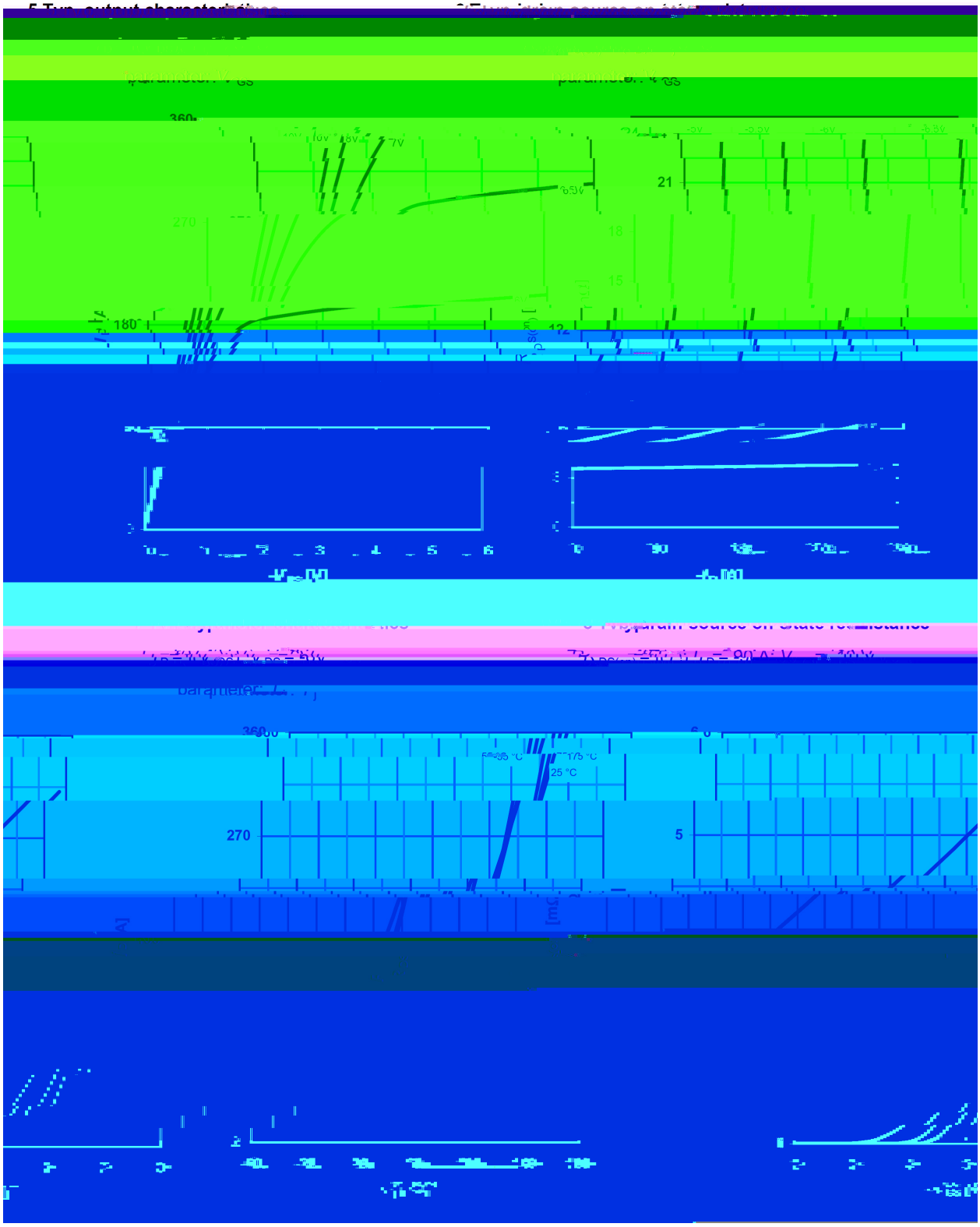
Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Gate to source charge	Q_{gs}	V_{DD}=-24V, I_D=-90A, V_{GS}=0 to -10V		42	55	nC
Gate to drain charge	Q_{gd}			10	20	nC
Gate charge total	Q_g			100	130	nC
Gate plateau voltage	$V_{plateau}$			-5.3		V
Diode continous forward current[2)]	I_S	T_C=25°C			-90	A
Diode pulse current[2)]	$I_{S,pulse}$				-360	A
Reverse recovery time[2)]	t_{rr}	V_R=-15V, I_F=-50A, di_F/dt =-100A/ s		50		nS
Reverse recovery charge[2)]	Q_{rr}			70		nC

1) Current is limited by bondwire; with an R_{JC} = 1.1K/W the chip is able to carry -143A at 25°C.
2) Defined by design. Not subject to production test.
3) Device on 40 mm x 40 mm x 1.5 mm epoxy PCB FR4 with 6 cm2 (one layer, 70 m thick) copper area for drain connection. PCB is vertical in still air.

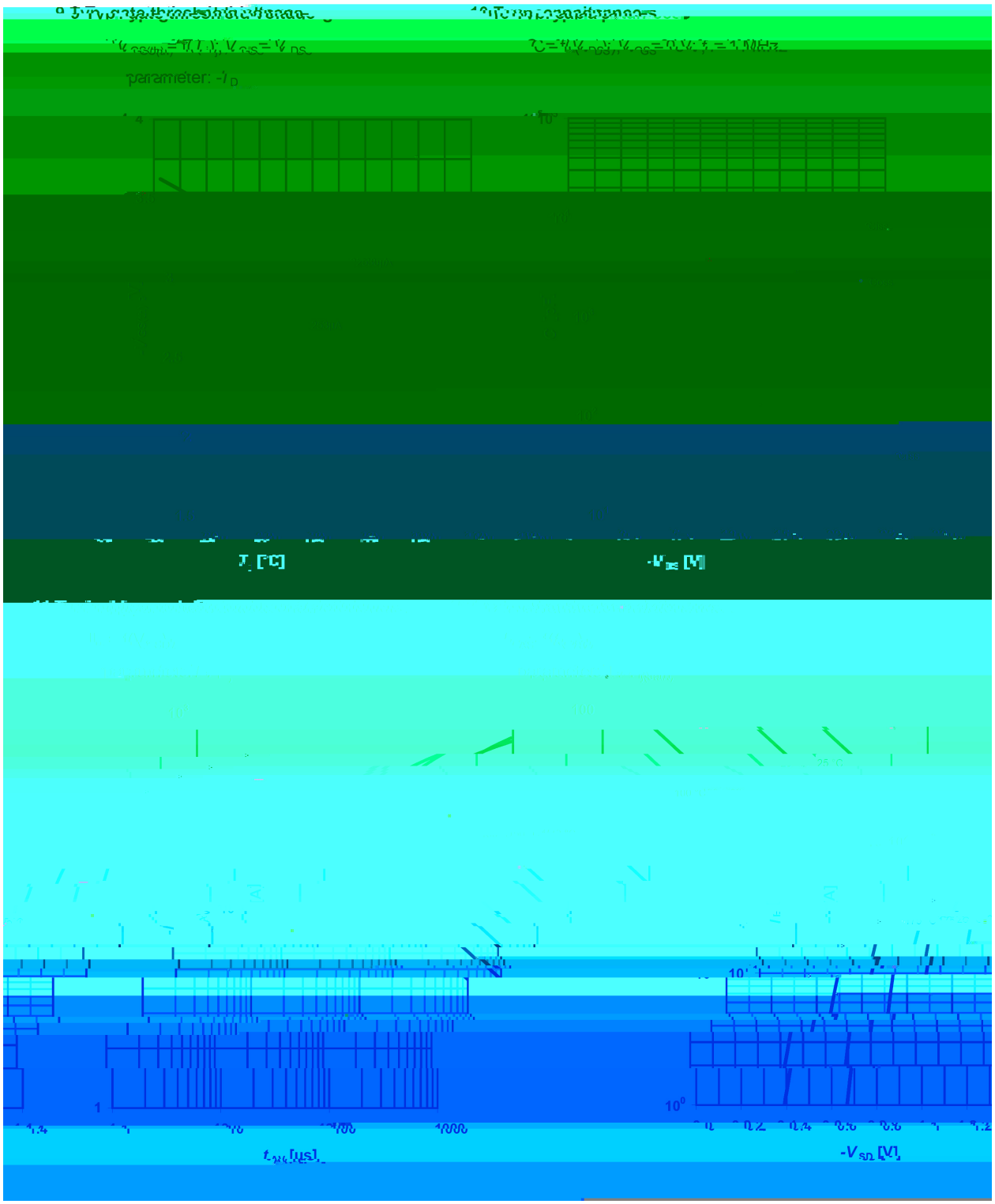
/ Electrical Characteristic Curve



/ Electrical Characteristic Curve



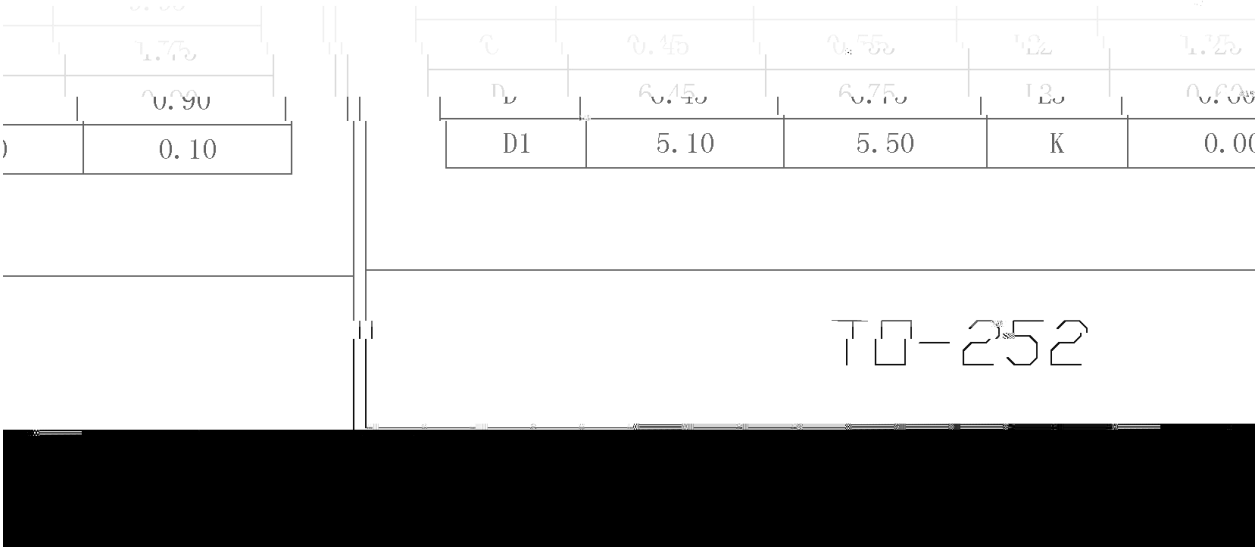
/ Electrical Characteristic Curve



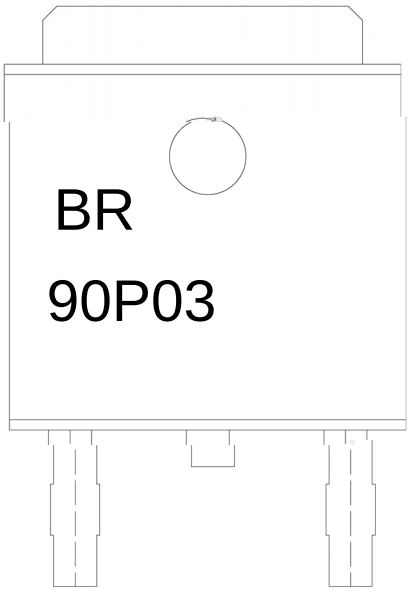
/ Package Dimensions



	0.90			
	0.10	D1	5.10	5.50	K	0.00



/ Marking Instructions



BR

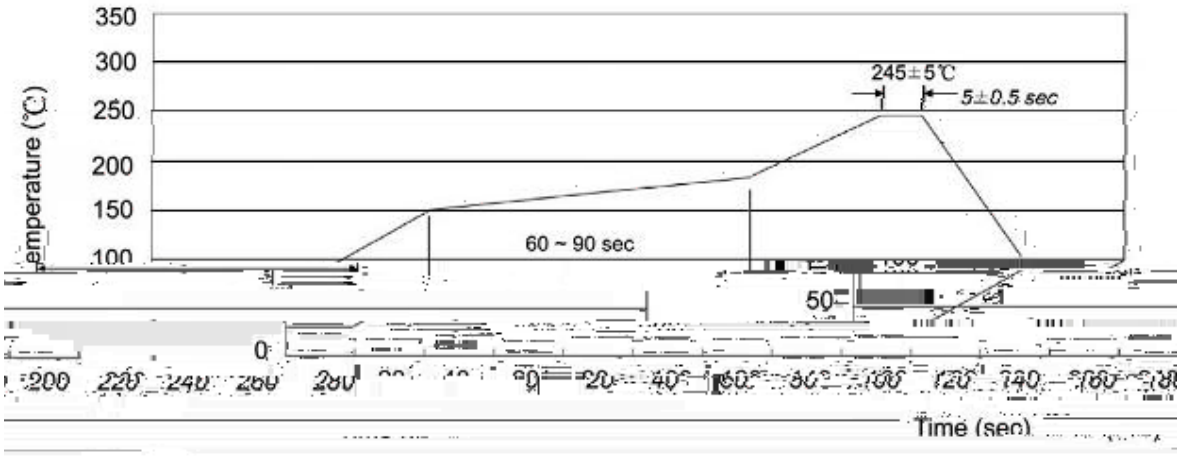
90P03

****

Note:

BR:	Company Code
90P03:	Product Type.
****:	Lot No. Code, code change with Lot No.

( ) / Temperature Profile for IR Reflow Soldering(Pb-Free)



			Note:	
1	150 180	60 90sec;	1.Preheating:150~180	, Time:60~90sec.
2	245±5	5±0.5sec;	2.Peak Temp.:245±5	, Duration:5±0.5sec.
3	2 10 /sec.		3. Cooling Speed: 2~10 /sec.	

/ Resistance to Soldering Heat Test Conditions

260±5	10±1 sec.	Temp.:260±5	Time:10±1 sec

/ Packaging SPEC.

/ BULK

Package Type 封装形式	Units 包装数量					Dimension 包装尺寸 (unit: mm³)		
	只 卷盘	卷盘 盒	只 盒	盒 箱	只 箱		盒	箱

/ TUBE

Package Type 封装形式	Units 包装数量					Dimension 包装尺寸 (unit: mm³)		
	只 套管	套管 盒	只 盒	盒 箱	只 箱	套管	盒	箱

/ Notices